Title: **JP10082707A2: PRESSURE DETECTOR**

Derwent Title: Pressure detector using sensor chip as sensor element or strain gauge - has passive-state film formed on gas-contact face of diaphragm of pressure detector using sensor chip to prevent corrosion, or water content emission from, or catalytic action at gas-contact face [Derwent Record]

Country: **JP** Japan
Kind: **A** (See also: JP03403294B2)

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Application Number: **JP1996000238706**

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Priority Number: 1996-09-10 **JP1996000238706**

Abstract: PROBLEM TO BE SOLVED: To eliminate the possibility of lowering the quality of product even a pressure detector is applied to a semiconductor production process, by forming a passive film on the gas-contact face of a stainless steel diaphragm having specified dimensions provided on a diaphraqm base.

SOLUTION: A diaphragm 3 of about 50μm thick having an inside diameter of about 10mm is made of stainless steel and has a gas-contact face 3a on which a passive film 3b of chromium oxide, a fluorinated passive film 3b or a mixed oxide passive film 3b of aluminum oxide and chromium oxide is formed. After forming the diaphragm 3 integrally with a diaphragm base 4, the diaphragm base 4 formed with the passive film 3b and a sensor base 1 are abutted against the gas contact face 3a of the diaphragm 3 and the entire circumference of the side wall face is welded 8. Subsequently, an oil injection hole 1b is filled with a pressure transmission medium (silicon oil) 5 and a sealing body (ball) 6 is welded 10 to the sensor base 1 thus sealing the silicon oil 5 hermetically.

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INPADOC Legal Status: None **Get Now:** Family Legal Status Report

Designated Country: AT BE CH DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE

Family: Show 16 known family members

Other Abstract None

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(54) PRESSURE DETECTOR

(57) Abstract:

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